



FCX495Q

150V NPN MEDIUM POWER TRANSISTOR IN SOT89

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

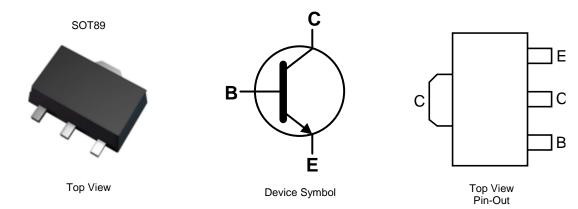
- BV_{CEO} > 150V
- I_C = 1A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < 300mV @ 0.5A
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.052 grams (Approximate)

Application

Low Loss Power Switching



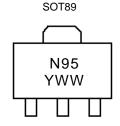
Ordering Information (Notes 4 and 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FCX495QTA	N95	7	12	1.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



N95 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 8 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

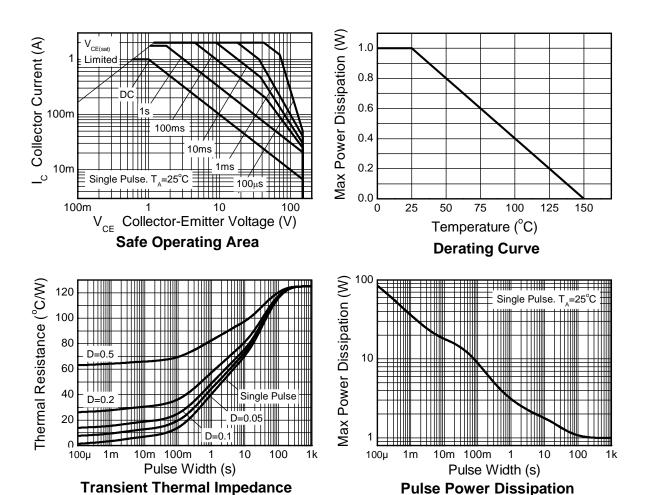
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	170	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current	Ісм	2	Α
Continuous Base Current	I _B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector Power Dissipation	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{0JL}	10.01	°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-65 to +150	°C

Notes: 6. For the device mounted on 15mm x 15mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions. 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

Thermal Characteristics and Derating Information





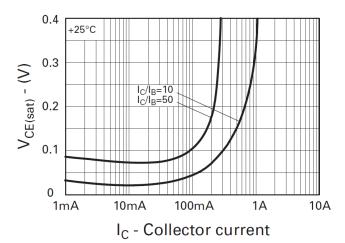
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	170	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	150	_	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	_	_	V	$I_E = 100 \mu A$
Collector Cut-Off Current	I _{CBO}	_	_	100	nA	V _{CB} = 150V
Emitter Cut-Off Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5.6V$
Emitter Cut-Off Current	I _{CES}	_	_	100	nA	V _{CE} = 150V
		100	_	_	_	$I_C = 1 \text{mA}, V_{CE} = 10 \text{V}$
DC Current Transfer Static Ratio (Note 8)	h	100	_	300	_	$I_C = 250 \text{mA}, V_{CE} = 10 \text{V}$
DC Current Transfer Static (Natio (Note 6)	h _{FE}	50	_	_	_	$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$
		10	_		_	$I_C = 1A, V_{CE} = 10V$
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	_	_	0.2	V	$I_C = 250 \text{mA}, I_B = 25 \text{mA}$
Collector-Entitler Saturation Voltage (Note 8)		_	_	0.3	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}		_	1.0	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn-On Voltage (Note 8)	$V_{BE(on)}$	_	_	1.0	V	$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$
Transitional Frequency	f _T	100	_	_	MHz	$I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V}$ f = 100MHz
Output Capacitance	C_{obo}	_	_	10	pF	$V_{CB} = 10V$, $f = 1MHz$

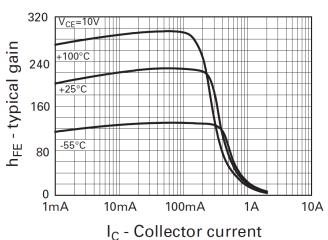
Note: 8. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



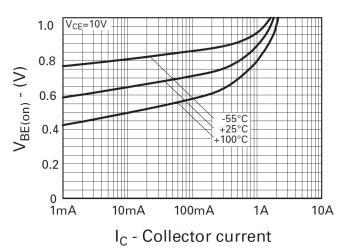
Typical Electrical Characteristics



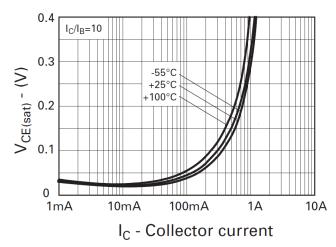
V_{CE(sat)} vs. I_C



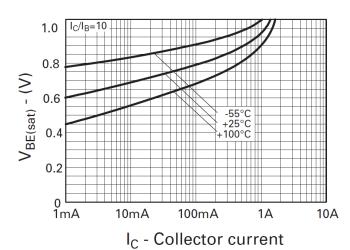
h_{FE} vs. I_C



V_{BE(on)} vs. I_C



V_{CE(sat)} vs. I_C



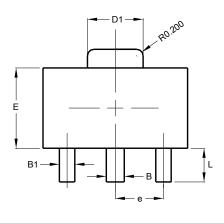
V_{BE(sat)} vs. I_C

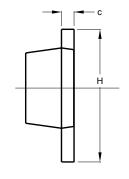


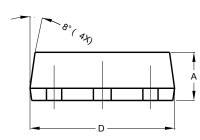
Package Outline Dimensions

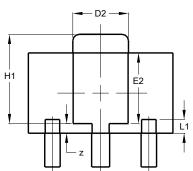
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







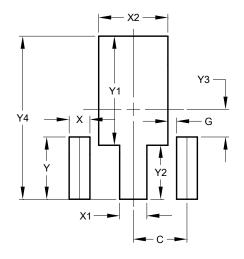


SOT89				
Dim	Min	Max	Тур	
Α	1.40	1.60	1.50	
В	0.50	0.62	0.56	
B1	0.42	0.54	0.48	
С	0.35	0.43	0.38	
D	4.40	4.60	4.50	
D1	1.62	1.83	1.733	
D2	1.61	1.81	1.71	
Е	2.40	2.60	2.50	
E2	2.05	2.35	2.20	
е	-	-	1.50	
Н	3.95	4.25	4.10	
H1	2.63	2.93	2.78	
L	0.90	1.20	1.05	
L1	0.327	0.527	0.427	
Z	0.20	0.40	0.30	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value		
Dilliensions	(in mm)		
С	1.500		
G	0.244		
X	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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